





DUAL COMPLEMENTARY PRE-BIASED TRANSIS

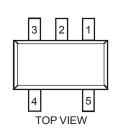
Features

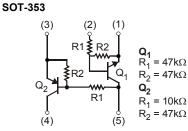
- **Epitaxial Planar Die Construction**
- Surface Mount Package Suited for Automated Assembly
- Simplifies Circuit Design and Reduces Board Space
- Lead Free/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-353
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed Over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4 Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)







Schematic and Pin Configuration

Maximum Ratings, Total Device @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_D	150	mW
Thermal Resistance, Junction to Ambient Air (Note 3)	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, Pre-Biased NPN Transistor, Q₁ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	Vcc	50	V
Input Voltage	V _{IN}	-10 to +40	V
Output Current	I ₀	30	mA
Collector Current	I _{C(MAX)}	100	mA

Maximum Ratings, Pre-Biased PNP Transistor, Q₂ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	-50	V
Input Voltage	V _{IN}	-40 to +6	V
Output Current	I ₀	-100	mA
Collector Current	I _{C(MAX)}	-100	mA

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics, Pre-Biased NPN Transistor, Q₁ @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	$V_{I(off)}$		_	0.5	V	$V_{CC} = 5V, I_{O} = 100 \mu A$
input voitage	V _{I(on)}	3	_	_	V	$V_O = 0.3V$, $I_O = 2mA$
Output Voltage	V _{O(on)}		0.1	0.3	V	$I_0/I_1 = 10 \text{mA}/0.5 \text{ mA}$
Input Current	II		_	0.18	mA	V _I = 5V
Output Current	I _{O(off)}	_	_	0.5	μΑ	$V_{CC} = 50V, V_{I} = 0V$
DC Current Gain	Gı	68	_	_	_	$V_{O} = 5V, I_{O} = 5mA$
Gain-Bandwidth Product	f⊤	_	250	_	MHz	$V_{CE} = 10V$, $I_{E} = -5mA$, $f = 100MHz^*$
Input Resistance	R ₁	32.9	47	61.1	kΩ	_
Resistance Ratio	R ₂ /R ₁	0.8	1	1.2	_	_

^{*}Characteristic of Transistor – for reference only.

Electrical Characteristics, Pre-Biased PNP Transistor, Q2 @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	$V_{I(off)}$		_	-0.3	V	$V_{CC} = -5V$, $I_{O} = -100\mu A$
input voitage	V _{I(on)}	-1.4	_		٧	$V_O = -0.3V$, $I_O = -1mA$
Output Voltage	V _{O(on)}	_	-0.1	-0.3	V	$I_{O}/I_{I} = -5\text{mA}/-0.25 \text{ mA}$
Input Current	l _l	_	_	-0.88	mA	V _I = -5V
Output Current	I _{O(off)}	_	_	-0.5	μΑ	$V_{CC} = -50V, V_{I} = 0V$
DC Current Gain	GI	68	_	_	_	$V_{O} = -5V, I_{O} = -5mA$
Gain-Bandwidth Product	f _T	_	250	_	MHz	$V_{CE} = -10V$, $I_{E} = 5mA$, $f = 100MHz^*$
Input Resistance	R ₁	7	10	13	kΩ	_
Resistance Ratio	R ₂ /R ₁	3.7	4.7	5.7	_	_

^{*}Characteristic of Transistor - for reference only.

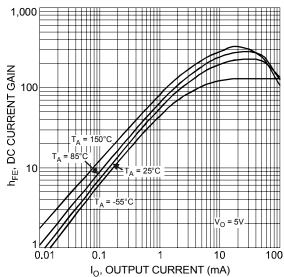


Fig. 1 Typical DC Current Gain vs. Output Current (Q1, NPN)

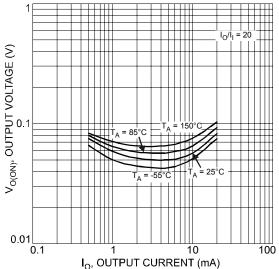
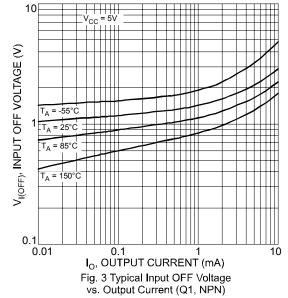
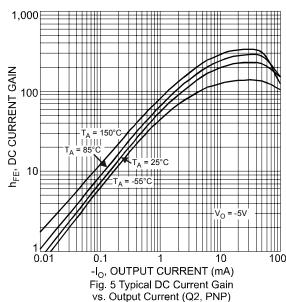
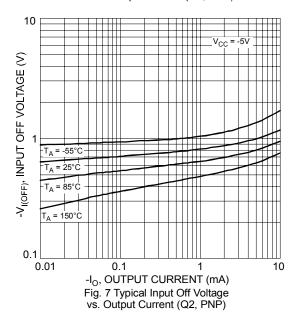


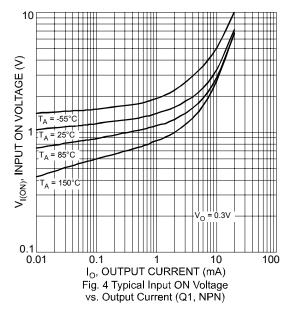
Fig. 2 Typical Output Voltage vs. Output Current (Q1, NPN)

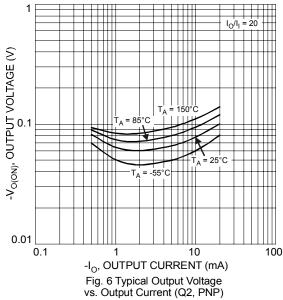


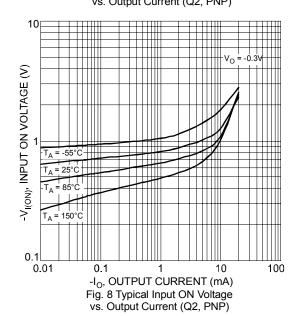












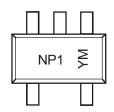


Ordering Information (Note 4)

Device	Packaging	Shipping
UMC4N-7	SOT-353	3000/Tape & Reel

Notes: 4. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

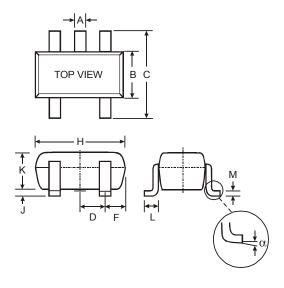


NP1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Kev

Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	l	J	\	/	V	V	>	(`	1	Z	7
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-353						
Dim	Min	Max				
Α	0.10	0.30				
В	1.15	1.35				
С	2.00	2.20				
D	0.65 Nominal					
F	0.30	0.40				
Н	1.80	2.20				
J		0.10				
K	0.90	1.00				
L	0.25	0.40				
М	0.10	0.25				
α	0°	8°				
All Dimensions in mm						

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